

BUK7219-55A

N-channel TrenchMOS standard level FET Rev. 02 — 3 February 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

Motors, lamps and solenoids

1.4 Quick reference data

Table 1. **Quick reference**

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|--|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | - | 55 | V |
| I_D | drain current | $V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> and <u>3</u> | - | - | 55 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | - | 114 | W |
| Avalanc | he ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 49 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped | - | - | 120 | mJ |
| Static ch | aracteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V; } I_D = 25 \text{ A;}$ $T_j = 175 \text{ °C;}$ see Figure 12 and 13 | - | - | 38 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12 and 13 | - | 16 | 19 | mΩ |



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol | | |
|------|--------|-----------------------------------|--------------------|----------------|--|--|
| 1 | G | gate | | _ | | |
| 2 | d | drain | mb | D | | |
| 3 | S | source | | | | |
| mb D | D | mounting base; connected to drain | 1 3 | mbb076 S | | |
| | | | SOT428 (DPAK) | | | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|---|---------|
| | Name | Description | Version |
| BUK7219-55A | DPAK | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|------------|-----|-----|------|
| V_{DS} | drain-source voltage | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ | | - | 55 | V |
| V_{DGR} | drain-gate voltage | $R_{GS} = 20 \text{ k}\Omega$ | | - | 55 | V |
| V_{GS} | gate-source voltage | | | -20 | 20 | V |
| I_D | drain current | T _{mb} = 100 °C; V _{GS} = 5 V; see <u>Figure 1</u> | | - | 39 | Α |
| | | T _{mb} = 25 °C; V _{GS} = 5 V; see <u>Figure 1</u> and <u>3</u> | | - | 55 | Α |
| I _{DM} | peak drain current | T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see <u>Figure 3</u> | <u>[1]</u> | - | 250 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | 114 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| Avalanche | ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 49 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped | | - | 120 | mJ |
| Source-dr | ain diode | | | | | |
| Is | source current | T _{mb} = 25 °C | | - | 55 | Α |
| I _{SM} | peak source current | $t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$ | | - | 250 | Α |

^[1] Peak drain current is limited by chip, not package.

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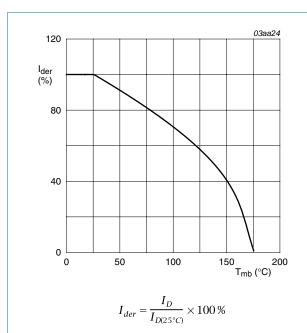
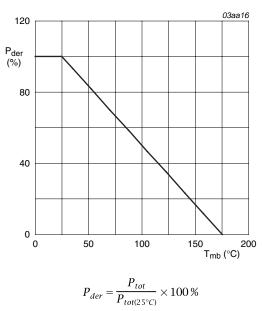
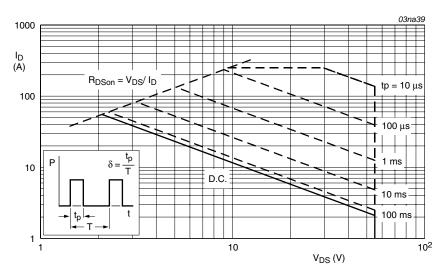


Fig 1. Normalized continuous drain current as a function of mounting base temperature



Normalized total power dissipation as a Fig 2. function of mounting base temperature



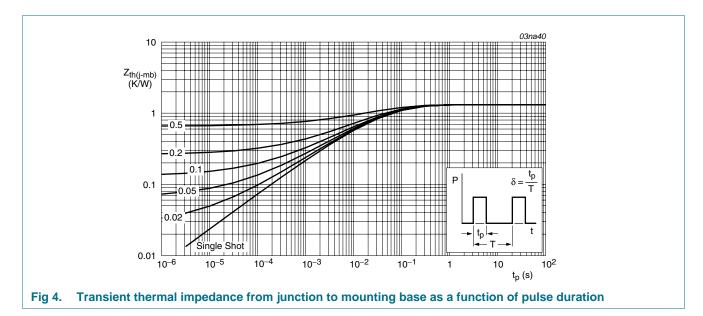
 $T_{amb} = 25$ °C; I_{DM} is single pulse

Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|--------------|-----|------|-----|------|
| $R_{\text{th(j-mb)}}$ | thermal resistance from junction to mounting base | | - | - | 1.3 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | see Figure 4 | - | 71.4 | - | K/W |



6. Characteristics

Table 6. Characteristics

| Table 6. | Characteristics | | | | | |
|---------------------|----------------------------------|--|-----|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | racteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | 55 | - | - | V |
| | breakdown voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$ | 50 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 11</u> | 2 | 3 | 4 | V |
| | | $I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 11</u> | - | - | 4.4 | V |
| | | $I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11 | 1 | - | - | V |
| I _{DSS} | drain leakage current | $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.05 | 10 | μΑ |
| | | V _{DS} = 55 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 500 | μΑ |
| I _{GSS} | gate leakage current | $V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}$ | - | 2 | 100 | nΑ |
| | | $V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 25 \text{ °C}$ | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 175 °C; see Figure 12 and 13 | - | - | 38 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12 and 13 | - | 16 | 19 | mΩ |
| Dynamic | characteristics | | | | | |
| C _{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ | - | 1581 | 2108 | рF |
| C _{oss} | output capacitance | T _j = 25 °C; see <u>Figure 15</u> | - | 372 | 446 | pF |
| C _{rss} | reverse transfer capacitance | | - | 221 | 303 | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$ | - | 16 | - | ns |
| t _r | rise time | $R_{G(ext)} = 10 \Omega$; $T_j = 25 °C$ | - | 70 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 57 | - | ns |
| t _f | fall time | | - | 41 | - | ns |
| L _D | internal drain inductance | measured from drain lead from package to centre of die; $T_j = 25$ °C | - | 2.5 | - | nΗ |
| L _S | internal source inductance | measured from source lead from package to source bond pad; $T_j = 25 ^{\circ}\text{C}$ | - | 7.5 | - | nΗ |
| Source-di | rain diode | | | | | |
| V _{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 14 | - | 0.85 | 1.2 | V |
| t _{rr} | reverse recovery time | I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C | - | 48 | - | ns |
| Q _r | recovered charge | | - | 106 | - | nC |

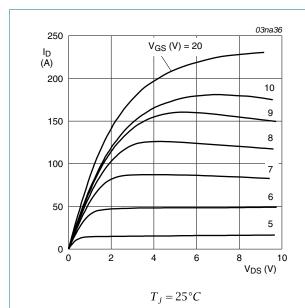


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

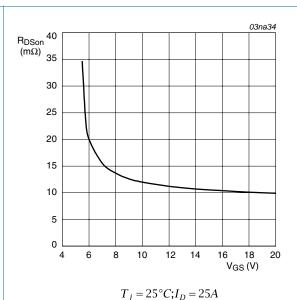
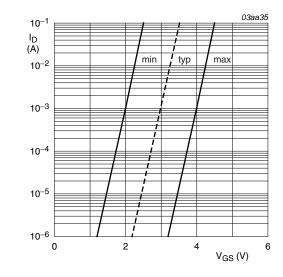
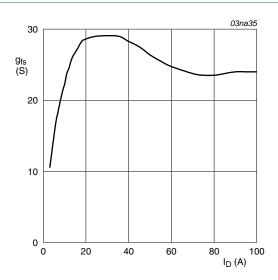


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; V_{DS} = 25V$

Fig 8. Forward transconductance as a function of drain current; typical values

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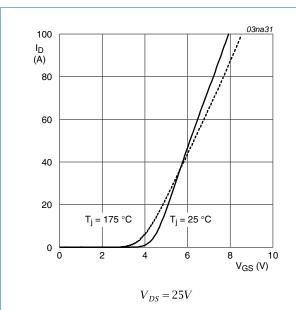
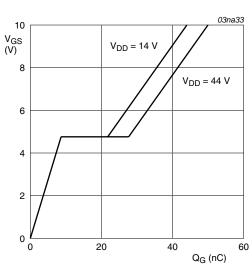


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25^{\circ}C; I_D = 25A$

Fig 10. Gate-source voltage as a function of turn-on gate charge; typical values

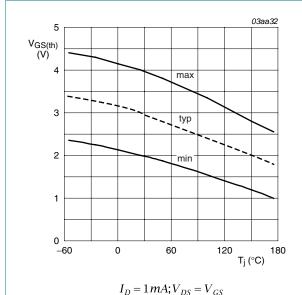


Fig 11. Gate-source threshold voltage as a function of junction temperature

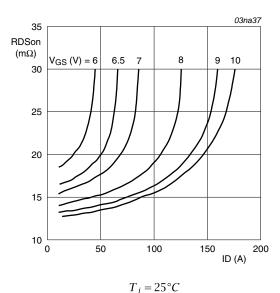


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

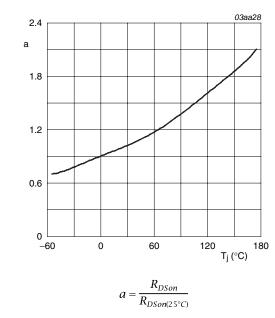


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

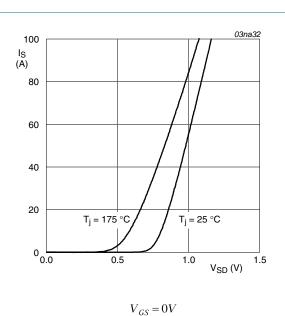
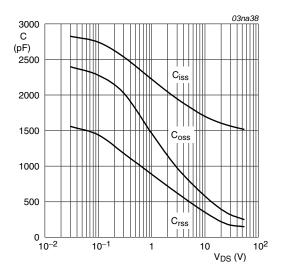


Fig 14. Reverse diode current as a function of reverse diode voltage; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

7. Package outline

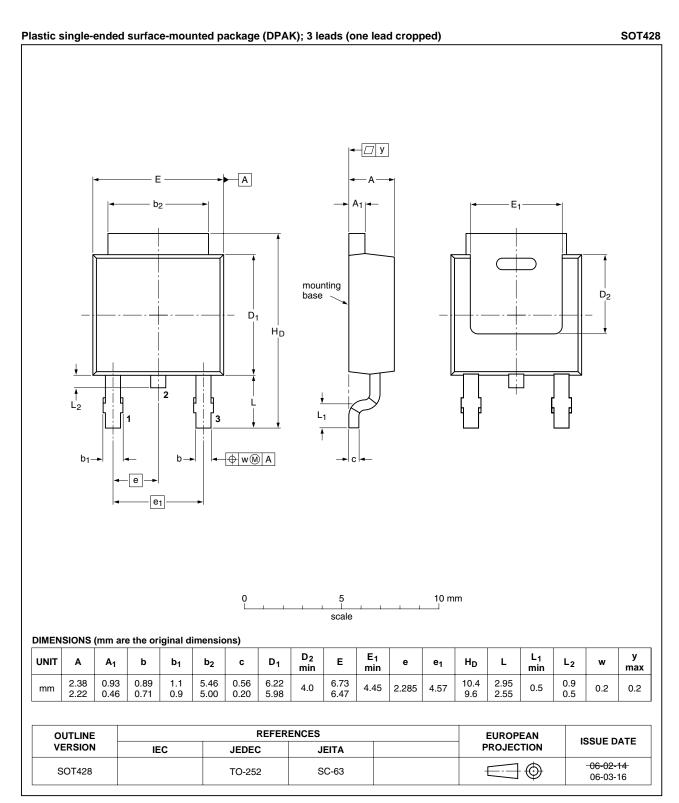


Fig 16. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|------------------------------------|---|--------------------------|----------------------|-----------------|
| BUK7219-55A_2 | 20100203 | Product data sheet | - | BUK7219-55A-01 |
| Modifications: | The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. | | | |
| | Legal texts | have been adapted to the | new company name whe | re appropriate. |
| BUK7219-55A-01 (9397 750 07575) | 20001002 | Product specification | - | - |

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9.1 Data sheet status

| Document status [1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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